

DIODE MODULE

DD(KD)60HB120/160

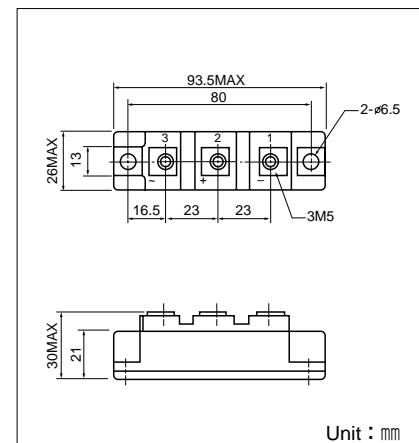
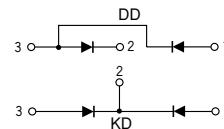
UL:E76102(M)

Power Diode Module **DD60HB** series are designed for various rectifier circuits. **DD60HB** has two diode chips connected in series and the mounting base is elctrically isolated from elements for simple heatsink construction. Wide voltage ratage up to, 1,600V is avaialble for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Battery chargers, DC motor drives



■ Maximum Ratings

($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Item	Ratings		Unit
		DD60HB120	DD60HB160	
V_{RRM}	Repetitive Peak Reverse Voltage	1200	1600	V
V_{RSM}	Non-Repetitive Peak Reverse Voltage	1350	1700	V

Symbol	Item	Conditions	Ratings	Unit
$I_{F(AV)}$	Average Forward Current	Single phase, half wave, 180° conduction, $T_c : 111^\circ\text{C}$	60	A
$I_{F(RMS)}$	R.M.S. Forward Current	Single phase, half wave, 180° conduction, $T_c : 111^\circ\text{C}$	95	A
I_{FSM}	Surge Forward Current	½ cycle, 50/60Hz, peak value, non-repetitive	1100/1200	A
I^2t	I^2t	Value for one cycle of surge current	6000	A^2s
T_j	Junction Temperature		-40 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40 to +125	$^\circ\text{C}$
V_{iso}	Isolation Breakdown Voltage (R.M.S.)	A.C.1minute	2500	V
M_t	Mounting (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	$\text{N}\cdot\text{m}$ (kgf·cm)
	Terminal (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	
Mass			170	g

■ Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{RRM}	Repetitive Peak Reverse Current, max.	at V_{DRM} , single phase, half wave. $T_j=150^\circ\text{C}$	20	mA
V_{FM}	Forward Voltage Drop, max.	Foward current 180A, $T_j=25^\circ\text{C}$, Inst. measurement	1.35	V
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to case	0.50	$^\circ\text{C}/\text{W}$

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